

METHOD FOR MANUFACTURING A FILM ON A SUPPORT HAVING A NON-FLAT SURFACE

FIELD OF THE INVENTION

5 The present invention relates to a method for manufacturing a film on a support having a non-flat surface.

PRIOR ART

10 The production of a film, notably monocrystalline, on a support is not an easy thing when said film has an interface surface with the support which is not flat, that is to say that said surface of the support comprises at least one curvature and/or a recessed or relief pattern.

15 This particular topology lends itself poorly to bonding and laminating methods, the trend is generally towards techniques consisting in forming the film by deposition on said support.

20 It is however necessary to ensure, apart from good mechanical strength of the film vis-à-vis the support, sufficiently good crystalline quality of the film. Yet, the crystalline quality of the film strongly depends on the support on which the deposition is operated and notably its surface. This is all the more true when monocrystalline films formed by epitaxy are considered. In this situation, the very nature of the support, through the necessity of having an appropriate crystalline structure and lattice parameters suited to the film that it is wished to deposit, is particularly crucial. The list of candidates capable of playing the role of support becomes very limited, to the point in certain specification cases of not being able to find a solution.

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DESCRIPTION OF THE INVENTION

One aim of the invention is thus to conceive a method for manufacturing a film on a support having a non-flat surface, while ensuring both good crystalline quality of the film and a quite extended choice as regards the nature of the support.

30 To this end, the invention proposes a method for manufacturing a film on a support having a non-flat surface, characterised in that it comprises:

- the supply of a donor substrate having a non-flat surface,
- the formation of an embrittlement zone in the donor substrate so as to delimit said film to transfer,
- 35 - the formation of the support by deposition on the non-flat surface of the film to transfer,
- the detachment of the donor substrate along the embrittlement zone, so as to transfer said film onto the support.

According to one embodiment, said method further comprises the deposition of an intermediate layer on the non-flat surface before the deposition of the support.

The formation of the embrittlement zone is advantageously carried out by implantation of ionic species in the donor substrate.

5 Said implanted ionic species may be hydrogen and/or helium.

According to one embodiment, the detachment of the donor substrate is caused by a heat treatment.

In this case, the deposition of the support is advantageously implemented with a thermal budget lower than that of the detachment heat treatment.

10 The transferred film may be made of a material selected from semiconductor materials, piezoelectric materials, magnetic materials and functional oxides.

In a particularly advantageous manner, the transferred film is monocrystalline.

The thickness of the transferred film is generally comprised between 100 nm and 10 μm , preferably between 100 nm and 1 μm .

15 The support may be made of a material selected from metals, glasses and ceramics.

The support typically has a thickness comprised between 1 and 50 μm .

20 Preferably, the material of the support is chosen to have a difference in thermal coefficient vis-à-vis the material of the transferred film less than $5 \times 10^{-6} \text{ K}^{-1}$ in absolute value.

The deposition of the support may be implemented by one of the following techniques: physical vapour deposition, chemical vapour deposition, electrochemical deposition, spin coating, lacquering and spraying.

25 According to one embodiment of the invention, the surface of the film to transfer has at least one curved portion.

According to one embodiment of the invention, the surface of the film to transfer has at least one recessed or relief pattern.

According to one embodiment of the invention, the surface of the film to transfer has a texture characterised by a roughness greater than 1 nm rms.

30 According to one embodiment, the non-flat surface of the film to transfer is obtained (for example by etching of the donor substrate) after the formation of the embrittlement zone.

35 According to one embodiment, the non-flat surface of the film to transfer is obtained (for example by etching of the donor substrate) before the formation of the embrittlement zone.

The residue of the donor substrate at the end of the detachment may be recycled with a view to the implementation of a new film having a non-flat surface on a support; before said recycling, the residue of the donor substrate is subjected to an operation of

regeneration of its surface involving a removal of material that is substantially zero or conforming to the topology of said residue.

According to one embodiment, the donor substrate comprises a plurality of pads laid out on the surface of a wafer, each pad comprising an embrittlement zone delimiting a
5 respective film to transfer, and the support is deposited on the surface of the whole of said pads.

According to a particular embodiment, the deposition of the support includes the successive deposition of at least two layers of different materials.

According to one embodiment, the method comprises, after the detachment of the
10 donor substrate, the deposition of an additional film on the face of the transferred film opposite to the support.

Another object relates to an intermediate structure obtained after deposition of the support on the donor substrate. Said structure comprises:

- a donor substrate including an embrittlement zone delimiting a superficial film and
15 - a support covering said film,
and the interface between the film and the support is not flat.

DESCRIPTION OF THE FIGURES

Other characteristics and advantages of the invention will become clear from the
20 detailed description that follows, with reference to the appended drawings, in which:

- figure 1A is a schematic sectional view of a donor substrate comprising a surface having recessed patterns;
- figures 1B and 1C illustrate in a schematic manner two alternatives of an embrittlement zone formed in the donor substrate of figure 1A;
- 25 - figure 1D illustrates in a schematic manner the support deposited on the donor substrate of figure 1B;
- the structure 1E illustrates an alternative of figure 1D, in which an intermediate layer has been deposited between the donor substrate and the support;
- figure 1F illustrates in a schematic manner the structure resulting from the
30 detachment of the donor substrate of figure 1E along the embrittlement zone;
- figure 1G illustrates in a schematic manner the structure of figure 1F after the deposition of an additional film on the transferred film;
- figures 2A and 2B illustrate an alternative to figures 1A-1B, corresponding to a reversed order of the steps concerned;
- 35 - figure 3A is a schematic sectional view of a donor substrate comprising a curved surface;
- figure 3B illustrates in a schematic manner the formation of an embrittlement zone in the donor substrate of figure 2A;

- figure 3C illustrates in a schematic manner the deposition of the support on the donor substrate of figure 3B;
- figure 3D illustrates in a schematic manner the structure resulting from the detachment of the donor substrate along the embrittlement zone;
- 5 - figure 4A is a schematic sectional view of a donor substrate comprising a textured surface;
- figure 4B illustrates in a schematic manner the formation of an embrittlement zone in the donor substrate of figure 4A;
- figure 4C illustrates in a schematic manner the deposition of the support on the
10 donor substrate of figure 4B;
- figure 4D illustrates in a schematic manner the structure resulting from the detachment of the donor substrate along the embrittlement zone;
- figures 5A-5E illustrate in a schematic manner the steps of a method implemented according to one embodiment of the invention;
- 15 - figures 6A-6D illustrate in a schematic manner the steps of a method according to another embodiment of the invention,
- figures 7A-7G illustrate in a schematic manner the steps of a method according to another embodiment of the invention;
- figures 8A-8C illustrate in a schematic manner the steps of a method according to
20 another embodiment of the invention.

For reasons of legibility of the figures, the different elements are not necessarily represented to scale.

DETAILED DESCRIPTION OF EMBODIMENTS OF THE INVENTION

25 Generally speaking, the invention provides for the formation of the support by deposition on a non-flat donor substrate that has been embrittled beforehand so as to delimit a thin film. Said thin film is next transferred onto the support by detachment of the donor substrate. The support may be constituted of a single material or a stack of at least two different materials, deposited successively on the donor substrate.

30 The non-planeness of the surface of the donor substrate may be due to a curvature (concave or convex) of at least one part of said surface, and/or to the presence of at least one recessed or relief pattern extending from said surface, and/or instead a surface texturing, whether voluntary or not.

35 Figure 1A illustrates a donor substrate 10 which comprises at least one superficial portion constituted of the material intended to form the thin film. Although said donor substrate is represented in the form of a bulk substrate, it could also be formed of a stack of different materials, of which a superficial layer constituted of the material intended to

form the thin film. In particular, the thin film may correspond to a layer of this stack produced by epitaxy.

The surface 10a of said donor substrate 10 comprises a certain number of recessed patterns 100 (or relief patterns – not illustrated here) with respect to a reference plane.

5 The patterns may advantageously be formed by lithography and etching of the donor substrate. They may also for example be obtained by deposition using masks.

Advantageously, the material intended to form the thin film is selected from: semiconductor materials (for example: silicon, silicon carbide, germanium, III-V compounds such as AsGa, InP, GaN, II-IV compounds such as CdTe, ZnO), piezoelectric
10 materials (for example: LiNbO₃, LiTaO₃, PZT, PMN-PT), magnetic materials and functional oxides (for example: ZrO₂, SrTiO₃, YSZ, GaO₂). These examples are not limiting.

Preferably, the material intended to form the thin film is monocrystalline. It may also be polycrystalline, and in this case emphasis is often placed on optimising its conditions of formation in order to obtain for example a particular density and size of crystalline grains,
15 and/or instead a preferential crystalline orientation, and/or an optimised roughness.

An embrittlement zone 11, which delimits a superficial film 12 intended to be transferred, is formed in the donor substrate 10. Although envisaged here as carried out after the formation of the patterns, the formation of the embrittlement zone could be implemented before the formation of the patterns.

20 The thickness of the transferred film is defined by the depth of the embrittlement zone 11 in the donor substrate 10. Advantageously, this depth is comprised between 100 nm and 10 µm, preferentially between 100 nm and 1 µm.

The formation of the embrittlement zone 12 in the donor substrate 10 may be carried out by implantation of ionic species (shown schematically by the arrows in figure 1B)
25 through the surface 10a of the substrate. Advantageously, the implanted species are hydrogen ions and/or helium ions. The implantation energy makes it possible to define the depth of the implantation zone 11. The implantation dose is chosen in order to enable the detachment of the film 12 after the application of a suitable treatment. The implantation dose is chosen sufficiently low so as not to induce the formation of bubbles as of the
30 implantation step. The ionic species, the energy and the implantation dose are chosen as a function of the material of the donor substrate 10. These conditions have been the subject of numerous publications and are known to those skilled in the art.

If the implantation is carried out through the surface already having recessed and/or relief patterns, the embrittlement zone may follow substantially the same profile as these
35 patterns, the thickness of material between the surface and the embrittlement zone remains substantially constant.

The continuity of the film and its quality in the vicinity of the transition zones between adjacent patterns may depend in particular on the thickness ratios between the thickness

of the film and the amplitude of the relief. For a thick film (for example 2 μm) and a low step (for example 0.05 μm), the film 12 could appear substantially continuous, as represented in figure 1B. Conversely, for a thin film (for example 0.05 μm) and a high step (for example 2 μm), the film 12 will be likely to have discontinuities (cf. figure 1C), which is not moreover necessarily penalising depending on the targeted application. In certain situations, this phenomenon could be taken into account and it could preferably be ensured that the angle between the surface of the patterns and the surface of a reference plane is less than or equal to 45°.

Alternatively (cf. figure 2A), if the implantation is carried out through the surface 10a of the donor substrate 10 which is initially flat, and the recessed and/or relief patterns are formed from this surface after the implantation, the embrittlement zone is substantially flat. The etching of the patterns 100 has to be carried out later such that the depth of etching is less than the depth of the embrittlement zone 11 (cf. figure 2B), if a discontinuity of the film 12 is not desired.

In order to take account of the fact that several topological levels may be brought into play with regard to the embrittlement planes, configurations where the embrittlement zone is not single but multiple and/or extended could be envisaged. In the case of an embrittlement by implantation, this could be done easily through a multiple or extended choice of implantation energies.

With reference to figure 1D, a support 20 is formed on the surface of the film 12 which, at this stage, still forms part of the donor substrate 10.

In contrast to bonding techniques, the support does not pre-exist and is formed directly on the donor substrate. The following deposition techniques may be implemented for the formation of said support: physical vapour deposition (PVD), chemical vapour deposition (CVD), deposition by electrodeposition or electroforming, electroplating or electrochemical deposition (ECD), spin coating, lacquering and spraying. These techniques are known *per se* and will not be described in greater detail here, those skilled in the art being capable of selecting the technique the most suited as a function of the material of the support to deposit. Deposition techniques at relatively low temperature are preferred, in order not to initiate a premature detachment of the donor substrate.

Depending on the deposition technique chosen, the deposition may be conformal, that is to say that the free surface of the support substantially follows the same profile as the patterns, the thickness of material between the surface of the support and the surface of the donor substrate remaining substantially constant.

However if the deposited thickness is important (for example greater than or equal to 50 μm) with regard to the size of the topology (for example a step of 0.5 μm), the deposited thickness could appear constant, and consequently the free surface of the support will appear flat.

According to other embodiments, the deposition may have the effect of filling the recesses present on the surface of the donor substrate, resulting in a free surface of the substantially flat support. In this case, the support has a variable thickness.

The support is advantageously made of a material selected from metals (for example: Ni, Cu, Cr, Ag, Fe, Co, Zn, Al, Mo, W and alloys thereof), glasses and ceramics (for example: silica (SiO_2), alumina (Al_2O_3), polycrystalline AlN, polycrystalline silicon, polycrystalline SiC). These examples are not limiting.

The thickness of the support is typically comprised between 1 and 50 μm (this thickness being sufficiently low so that the support can be assimilated with a sheet), but may also be much greater.

Furthermore, care is taken that the adherence of the support on the donor substrate is sufficient in order to avoid the detachment of the support during the film transfer method. This adherence may be improved by the deposition of an adhesion layer on the donor substrate before the deposition of the support. For example, said adhesion layer may be made of one of the following materials: Ti, Cr, Pt, Ta, TiW, Si_3N_4 , TiN, CrCu.

More generally, an intermediate layer 21 may be deposited on the film 12 before the deposition of the support 20 (the final structure being represented in figure 1E). Apart from a potential adhesion function, such a layer may notably have the function of avoiding the diffusion of chemical species to the film 12 during the deposition of the support 20, and/or to form an electrical contact on the film 12, and/or to form an optical index jump, and/or instead to minimise a discontinuity in acoustic impedance. Naturally those skilled in the art are capable of choosing the suitable material and its thickness according to the mechanical, electrical, optical, thermal, acoustic or chemical function of the intermediate layer.

The thickness of said intermediate layer 21 is sufficiently low so that the rigidity of this layer does not penalise the flexibility of the support, when this criterion is important.

When an important difference exists between the thermal expansion coefficients of the support and the film (typically a difference greater than $5 \times 10^{-6} \text{ K}^{-1}$), the material of the support is chosen to demonstrate sufficient ductility in order that the transferred film does not suffer damage (for example of fissure type) during the transfer method. Sufficient ductility is taken to mean that the elastic limit of the support is less than the product of the elastic limit of the film and the thickness ratio between the film and the support.

With reference to figure 1F, the donor substrate 10 is next detached along the embrittlement zone 11, so as to transfer said film 12 onto the support 20. At the end of this detachment a residue 10' of the donor substrate remains, which may potentially be recycled with a view to another use.

The detachment is caused by a treatment of the stack of the support 20 on the donor substrate 10. Said treatment may be for example thermal, mechanical or a combination of

these two types of treatment. This type of treatment is well known notably within the context of the Smart Cut™ method and will thus not be described in detail here. In the case of a heat treatment, the thermal budget of this treatment is generally greater than the thermal budget of deposition of the support.

5 The film 12 may potentially serve as seed for the deposition of an additional film 13 (cf. figure 1G).

 The structure formed of the support 20 and the film 12 (and a potential additional film) may be used to form devices that notably have applications in microelectronics, photonics or optics. Such a structure may also enter into the manufacture of sensors or
10 transducers, or membranes for fuel cells.

 Figures 3A to 3D show in a schematic manner another embodiment of the transfer method, wherein the surface of the donor substrate has at least one curvature, concave or convex.

 The reference signs common with figures 1A to 2B designate the same elements,
15 which will thus not be described again in detail. In addition, the materials and methods described with reference to figures 1A to 2B are also applicable to the embodiment of figures 3A to 3D, such that they will not be described again in detail.

 With reference to figure 3A, the surface 10a of the donor substrate 10 is concave.

 With reference to figure 3B, an implantation of atomic species through the surface
20 10a has the effect of forming an embrittlement zone 11 within the donor substrate 10. Said embrittlement zone generally has a curvature substantially parallel to the surface of the donor substrate 10, the thickness of the film 12 to transfer being substantially constant. As indicated previously, the surface of the donor substrate may be made concave or convex after the formation of the embrittlement zone, which is then generally flat.

25 With reference to figure 3C, a support 20 is formed by deposition on the surface of the film 12 which, at this stage, still forms part of the donor substrate 10. As indicated previously, the deposition of the support may be preceded by the deposition of an intermediate layer (not represented).

 Depending on the deposition technique chosen, the deposition may be conformal,
30 that is to say that the free surface of the support has substantially the same curvature as the donor substrate, the thickness of material between the surface of the support and the surface of the donor substrate remaining substantially constant.

 With reference to figure 3D, the donor substrate 10 is next detached along the embrittlement zone 11, so as to transfer said film 12 onto the support 20. At the end of this
35 detachment a residue 10' of the donor substrate remains, which can potentially be recycled with a view to another use.

 The method of figures 3A to 3D is particularly interesting for the formation of curved parts. They may be for example coatings of optical parts, such as divergent or convergent

lenses or instead parabolic shaped mirrors. They may also be optical glasses for eye glasses or augmented reality glasses, or curved screens, or instead windscreen or cockpit elements for example.

Figures 4A to 4D show in a schematic manner another embodiment of the transfer method, wherein the surface of the donor substrate has a textured topology. Said topology may notably correspond to a roughness of the surface of the donor substrate, obtained voluntarily or not.

Reference signs common with figures 1A to 3D designate the same elements, which will not be described again in detail. In addition, the materials and methods described with reference to figures 1A to 2B are also applicable to the embodiment of figures 4A to 4D, such that they will not be described again in detail.

With reference to figure 4A, the surface 10a of the donor substrate 10 has a certain roughness, for example greater than or equal to 1 nm rms.

With reference to figure 4B, an implantation of atomic species through the surface 10a has the effect of forming an embrittlement zone 11 within the donor substrate 10. As indicated previously, the surface of the donor substrate may potentially be textured after the formation of the embrittlement zone.

With reference to figure 4C, a support 20 is formed by deposition on the surface of the film 12 which, at this stage, still forms part of the donor substrate 10. As indicated previously, the deposition of the support may be preceded by the deposition of an intermediate layer (not represented).

Depending on the deposition technique chosen, the deposition may be conformal, that is to say that the free surface of the support has substantially the same texture as the donor substrate, the thickness of material between the surface of the support and the surface of the donor substrate remaining substantially constant.

With reference to figure 4D, the donor substrate 10 is next detached along the embrittlement zone 11, so as to transfer said film 12 onto the support 20. At the end of this detachment a residue 10' of the donor substrate remains, which may potentially be recycled with a view to another use.

The method of figures 4A to 4D is particularly interesting for acoustic wave structures such as radiofrequency (RF) filters for example, and notably to avoid reflections of parasitic waves on the rear face of the substrates and or layers considered.

Below are described several examples (non-limiting) of application of the method according to the invention.

Example 1: formation of a lithium niobate film on a copper sheet

Lithium niobate (LiNbO_3) is a piezoelectric and pyroelectric material remarkable in that it conserves its piezoelectric properties up to high temperatures. Its Curie temperature

is 1140°C, whereas numerous other materials lose their properties as of temperature ranges of the order of 100 to 250°C.

It thus represents an interesting material for systems exploiting piezoelectricity and/or pyroelectricity in these temperature ranges. For example, they may be systems for recovering energy by recovery of the energy of vibrations and other deformations of a mechanical system operating in a hostile environment in temperature ranges above 250°C. They may also be piezo or pyroelectric sensors dedicated to the measurement of temperature, pressure or to the detection of gas.

This material is monocrystalline and of good quality when it is produced by drawing out of ingots then cut into bulk wafers of several hundreds of μm thickness. In thin films, when they are produced by deposition, they are in general polycrystalline, at best quasi-monocrystalline but very defective.

Numerous targeted structures have to follow a certain topology, such as for example that of a structured floating beam or instead a floating platform, shifted or set back with respect to the average level of the surface of the substrate.

A LiNbO_3 substrate 10 is provided. Trenches 100 are produced by etching in the substrate 10 in order to define the contours of a future suspended membrane (cf. figure 1A). Typically the trenches have widths of several tens of μm and their depth is comprised between 0.1 and 0.5 μm .

Helium ions are implanted in said substrate 10 so as to form an embrittlement zone 11 and delimit a thin LiNbO_3 film 12 (cf. figure 1B). The thickness of the film 12 is of the order of 0.3 μm .

An adhesion layer 21 constituted of a Cr/Cu alloy is deposited on the film 12 by a PVD technique. A copper sheet 20 is next deposited on said adhesion layer 21 by an electrochemical deposition technique (cf. figure 1E). The thickness of said sheet is of the order of 20 μm .

Next, an annealing is applied at a temperature of 300°C, in order to cause the detachment of the donor substrate 10 along the embrittlement zone 11.

30 Example 2: formation of a yttrium stabilised zirconia film on a nickel sheet

Yttrium stabilised zirconia (YSZ) is generally in the form of polycrystalline ceramic, and more rarely in the form of monocrystalline substrate.

One use of this material is based on its ion conduction properties. It then serves as solid membrane to play the role of electrolyte in SOFC (Solid Oxide Fuel Cell) systems. Such systems, when they have to be miniaturised (this is then known as micro-SOFC) have interest to evolve to membranes which are on the one hand thin, that is to say typically below several μm thickness, and on the other hand monocrystalline. Such systems operate at high temperature (typically 550-700°C) and are subjected to strong

thermomechanical loads. In order to make the membrane more resistant, it is advantageously given a corrugated shape thereby having a bellows topology, this shape making it possible to absorb deformations better by spring effect. Such a shaping may moreover have the beneficial effect of maximising the exposed surface available for the
5 desired electrochemical reactions.

A monocrystalline YSZ substrate 10 (cf. figure 7A) is supplied. Networks of trenches 100 are produced by etching in the substrate 10 in order to define the contours of the future bellows of the electrolyte membrane (cf. figure 7B). Typically the trenches 100 have widths of several tens of μm and their depth is of the order of 2 μm . The sides 100a of the
10 trenches, which will define the transition between the high zones and low zones of the bellows, are advantageously controlled to be inclined at more than 45° from the normal to the surface 10a. The trenches are spaced apart from each other by several tens of μm to form the desired corrugations.

Hydrogen ions are implanted in said substrate 10 so as to form an embrittlement
15 zone 11 and delimit a thin YSZ film 12 (cf. figure 7C). The thickness of the film 12 is of the order of 1 μm .

An adhesion layer 21 constituted of a Cr/Cu alloy is deposited on the film 12 by a PVD technique (cf. figure 7D). A nickel sheet 20 is next deposited on said adhesion layer 21 by an electrochemical deposition technique (cf. figure 7E). The thickness of said sheet
20 is of the order of 20 μm .

Next, an annealing is applied at a temperature of 300°C , in order to cause the detachment of the donor substrate 10 along the embrittlement zone 11 (cf. figure 7F).

The support 20 may next be etched so as to obtain the final bellows shape (cf. figure 7G).
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Example 3: formation of a monocrystalline silicon film on a curved glass sheet

In the field of the production of screens or other optical parts (lenses, mirrors, etc.), the production of non-flat or curved parts makes the use of thin films of monocrystalline materials such as silicon difficult. This example aims to make available a thin silicon film
30 on a glass sheet having a certain curvature. This silicon film could notably serve to produce high performance transistors, for example for the purposes of manufacturing high definition ultra-compact and curved screens.

A bulk monocrystalline silicon substrate 10 is provided.

The curved shape that it is wished to follow is produced by etching in this silicon
35 substrate. In the embodiment illustrated in figure 5A, the chosen shape is concave with a more marked rise on the edges. Any other profile – parabolic, elliptic, corrugated, etc. – is possible. This shape may be produced thanks to an etching by mechanical machining.

Those skilled in the art will know how to adapt the etching technique the most suited to the desired shape and dimension.

The substrate 10 is subjected to a thermal oxidation to produce a SiO_2 layer 14 of 0.2 μm thickness (cf. figure 5B).

5 Hydrogen ions are next implanted in said substrate 10 through the oxide layer 14 so as to form an embrittlement zone 11 and delimit a thin film 12 of monocrystalline silicon (cf. figure 5C). The thickness of the film 12 is of the order of 0.5 μm .

A sheet 20 made of silica (glass) is deposited on the film 12 by a deposition technique at low temperature, typically below 200°C so as not to cause an untimely detachment along the embrittlement zone (cf. figure 5D). The thickness of said sheet is of the order of 20 μm . The doping of the silica, for example using phosphorous or boron ions, makes it possible to better adjust the coefficient of thermal expansion of the glass to that of silicon in the case where high thermomechanical stresses were to appear. Those skilled in the art will know how to choose the doping level as well as the conditions and the deposition technique the most suited notably in terms of temperature and desired final thickness.

Next, an annealing is applied at a temperature of 500°C, in order to cause the detachment of the donor substrate 10 along the embrittlement zone 11 (cf. figure 5E).

20 Example 4: formation of a lithium tantalate film on a glass sheet

This example targets acoustic wave structures such as radiofrequency (RF) filters for example. In certain RF structures it is sought to avoid reflections of parasitic waves on the rear face of the substrates and or layers considered. One means consists in making geometrically imperfect the interfaces and rear surfaces notably by introducing voluntary texturings or other roughnesses. This constraint is difficult or even impossible to satisfy if the use of certain thin films of monocrystalline materials such as LiTaO_3 for example is envisaged, and this is so without resorting to the introduction of complex stacks of additional intermediate layers.

A bulk monocrystalline LiTaO_3 substrate 10 is supplied.

30 Hydrogen ions are implanted in said substrate 10 through the surface 10a so as to form an embrittlement zone 11 and to delimit a thin film 12 of monocrystalline LiTaO_3 (cf. figure 6A). The thickness of the film 12 is of the order of 1.5 μm .

A texturing of the surface 10a is created by photolithoetching (cf. figure 6B). In this example the implantation takes place before the texturing step but is could take place after as in the embodiment illustrated in figures 4A-4D.

Those skilled in the art will know how to adapt the technique the most suited to the shape and dimensions desired for the texture. It would be possible for example to choose a nanoimprint lithography technique to define patterns of characteristic slightly

submicronic lateral dimensions, over a depth of the order of 0.05 μm . In one alternative, the texturing is obtained by roughening by cathodic sputtering effect. According to another alternative, implemented preferably before the implantation step, the texturing may be obtained by a sanding of the surface of the substrate 10.

- 5 A sheet 20 made of silica is deposited on the film 12 by a deposition technique at low temperature, typically below 100°C so as not to cause an untimely detachment along the embrittlement zone (cf. figure 6C). The thickness of said sheet is of the order of 10 μm . Those skilled in the art will know how to choose in these conditions the deposition technique the most suited notably in terms of temperature and desired final thickness. As
10 an alternative, the sheet 20 may be made of metal instead of being made of silica.

Next, an annealing is applied at a temperature of the order of 200°C, in order to cause the detachment of the donor substrate 10 along the embrittlement zone 11 (cf. figure 6D).

15 Example 5: Case of a donor substrate comprising a plurality of pads

According to one embodiment of the invention, the non-flat topology of the donor substrate results from the formation of a plurality of pads 1001 laid out on the surface of a wafer 1000 (cf. figure 8A).

- 20 The pads are advantageously formed of a material selected from semiconductor materials, piezoelectric materials, magnetic materials and functional oxides. The pads are advantageously monocrystalline. Each pad may be put in place on the wafer by bonding, individually or collectively.

- 25 The pads may have any appropriate size and shape as a function of the targeted application. The pads may be laid out in a regular manner on the wafer, for example to form a sort of grid pattern.

- 30 The main surface of each pad 1001 is parallel to the main surface of the wafer 1000. However, in so far as the thickness of each pad is not controlled with sufficient precision, there may exist a slight difference in thickness from one pad to the next (for example of the order of 1 or 2 μm thickness). As a result, the surface constituted of all of the surfaces of the pads has differences in levels, typically in the form of steps (the amplitude of these variations has been voluntarily exaggerated in figure 8A). These different steps thus form a non-flat topology of the surface of the wafer.

- 35 In general, as described for example in the documents FR 3 041 364 and US 6,562,127, the pads are intended for the transfer of a superficial monocrystalline film onto a support final. To this end, an embrittlement zone 1011 is formed in each pad, before or after its putting in place on the wafer, to delimit a respective film 1012 to transfer, for example by an implantation such as described above.

Unlike the methods described in the aforementioned documents, which involve bonding of the main face of each pad on the final support, the invention proposes depositing the support 20 on all of the pads laid out on the surface of the wafer (cf. figure 8B). One is thus free of problems of assembly linked to the difference in height of the
5 different pads.

Next, each pad is detached along the respective embrittlement zone 1011, so as to transfer the corresponding film 1012 onto the support 20 (cf. figure 8c).

Whatever the embodiment considered, at the end of the detachment of the donor
10 substrate a residue 10' remains.

If a recycling of said donor substrate is envisaged, it is possible to implement reconditioning operations, notably with the aim of regenerating the surface of the donor substrate which could have been damaged during the detachment. These operations may notably comprise steps of cleaning, etching, annealing, smoothing and planarization, for
15 example by polishing.

In the case where the formation of the topology of the donor substrate has taken place before the embrittlement step, the residue of the donor substrate has a topology identical to the initial topology of the donor substrate. It may appear advantageous for questions of cost to conserve this topology (curvature, and/or recessed pattern and/or
20 texturing) that had been initially created in the donor substrate, with a view to avoiding having to reform it systematically after each recycling. In this case planarization methods are avoided, while favouring methods for removing material conformal in thickness, or even with substantially zero removal of material (that is to say below 30 nm), such as for example plasma etchings or smoothing annealings.

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